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P. 14/17

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant Zhu et al.	
District wy 1.5pp	Filing Date	Group
(Use Several Sheets if Necessary)	December 10, 2003	2891

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Examiner					_	Sub-	Filing
initial	No.	Patent No.	Date	Patentee	Class	class	Date
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<u> </u>	A2	6,232,196	5/12/01	Raaijmakers et al.		↓	
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	A6	6,596,653	7/22/03	Tan et al.		1:	
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Examiner		////	1 ** - * *	Date Considered		1	
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant: Zhu et al.	Group
(Use Several Sheets if Necessary)	Filing Date December 10, 2003	2891

Roreion Patent or Published Foreign Patent Application

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Examiner		Document	Publication	Country or			Translation
Initial	No.	No	Date	Patent Office	Class	class	Yes No
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		Other Doc	uments	
Examiner		:		
Initial	No.	Author, Title, Date, Place (e.g.	Journal) of Publication	
NVS	C1	U.S. Office Action mailed Aug	ist 6, 2003, from U.S. Applicati	on No. 10/058,897.
25KS		TAtty Dokt. NOVLP040X1/NV	LS-0006071 '	
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		[Atty Dokt. NOVLP040XI/NV	LS-000607]	
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1 1	1	High Aspect Ratio Structures".	Novellus Systems, Inc., filed O	ctober 11, 2002,
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant: Zhu et al.	
	Filing Date	Group
(Use Several Sheets if Necessary)	December 10, 2003	2891

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JAN 0 9 2006

Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant. Zhu et al.	
(Use Several Sheets if Necessary)	Filing Date December 10, 2003	Group 2891

Examiner
Initial
No. Author, Title, Date, Place (e.g. Journal) of Publication

C29
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Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888 Application No.: 10/733,858

Information Disclosure Statement By Applicant

Applicant: Zhu et al.

Group

(Use Several Sheets if Necessary)

Filing Date
December 10, 2003

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considered. Include copy of this form with next communication to applicant.

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orm 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888

Application No.:

Information Disclosure Statement By Applicant

Applicant: Zhu et al.

10/733,858

(Use Several Sheets if Necessary)

Filing Date December 10, 2003 Group 2891

Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Trans	lation
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
	B1	JP 2003-031,649	01.2003	Japan				

Other Documents

		Other Documents					
Examiner							
Initial	No.	<u> </u>					
26111	U.S. Office Action mailed August 6, 2003, from U.S. Application No. 10/058,897.						
75K5		[Atty Dckt. NOVLP040X1/NVLS-000607]					
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	C4	U.S. Office Action mailed August 10, 2004, from U.S. Application No. 10/271,333.					
L		[Atty Dckt. NOVLP054/NVLS-000719]					
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	C6	U.S. Office Action mailed June 29, 2005, from U.S. Application No. 10/728,569.					
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	C7	Papasouliotis et al., "Hydrogen-Based Phosphosilicate Glass Process for Gap Fill of					
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	C8	Guari et al., "Method of Preventing Structures Erosion During Multi-Step Gap Fill",					
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<u> </u>		10/2/16,987. [Atty Dckt. NOVLP053/NVLS-000706]					
Examiner	N	Date Considered					
	$Z \rangle_{z}$	3/19/06					

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Form 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888 Application No.:

Information Disclosure Statement By Applicant

(Use Several Sheets if Necessary)

Applicant: Zhu et al.

10/733,858

Filing Date Group December 10, 2003 2891

		Other Documents					
Examiner							
Initial	No.						
1/65	C15						
1)()		[Atty Dckt. NOVLP061/NVLS-000756]					
Ι΄.	C16	1 · · · · · · · · · · · · · · · · · · ·					
1		Systems, Inc., filed September 2, 2003, Application No. 10/654,113, pages 1-31.					
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<u> </u>		[Atty Dckt. NOVLP079/NVLS-002850]					
1	C19	1					
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1	C20	Bayman et al., "Process Modulation to Prevent Structure Erosion During Gap Fill",					
1		Novellus Systems, Inc., filed September 7, 2004, Application No. 10/935,909, pages					
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	1	Novellus Systems, Inc., filed September 21, 2004, Application No. 10/947,424, pages					
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1	C22	Hook et al., "The Effects of Fluorine on Parametrics and Reliability in a 0.18-µm					
	ļ	3.5/6.8 nm Dual Gate Oxide CMOS Technology", IEEE Transactions on Electron					
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<u> </u>	1	[Atty Dckt. NOVLP053/NVLS-000706]					
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1 1	1	Novellus Systems, Inc., filed June 22, 2005, Application No. 11/159,834, pages 1-29.					
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888 Application No.: 10/733,858

Information Disclosure Statement By Applicant Applicant: Zhu et al. 0//22,020

(Use Several Sheets if Necessary)

Filing Date
December 10, 2003

Group 2891

Other Documents

		Other Documents
Examiner		
Initial_	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BKS		U.S. Office Action mailed October 18, 2005, from U.S. Application No. 10/947,424. [Atty Dckt. NOVLP113/NVLS-2949]
BKS BKS	C30	Lang et al., "Using Water (H20) To Replace Oxygen (02) In A Silicon Dioxide (Si02) Thin Film Deposition Process for HDP STI Technology", Novellus Systems, Inc., filed November 9, 2005, Application No. 11/272,487, pages 1-25. [Atty Dkt No. NOVLP136/NVLS-3082].
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Examiner	1	Date Considered

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